Darlington Complementary Silicon Power Transistors

These devices are designed for general-purpose amplifier and low-speed switching motor control applications.

Features

- Similar to the Popular NPN 2N6284 and the PNP 2N6287
- Rugged RBSOA Characteristics
- Monolithic Construction with Built-in Collector-Emitter Diode
- These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	100	Vdc
Collector-Base Voltage	V _{CB}	100	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current – Continuous – Peak	I _C	20 40	Adc
Base Current	I _B	0.5	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	160 1.28	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.78	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

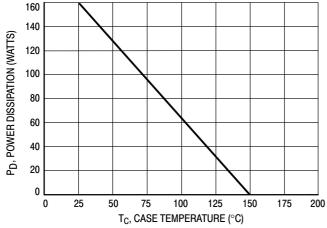


Figure 1. Power Derating

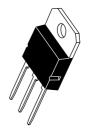
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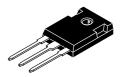
ON Semiconductor®

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DARLINGTON 20 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 100 VOLTS, 160 WATTS



SOT-93 (TO-218) CASE 340D



TO-247 CASE 340L STYLE 3

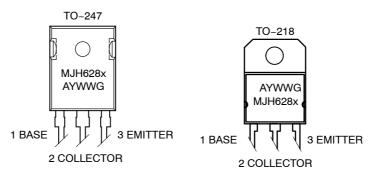
NOTE: Effective June 2012 this device will be available only in the TO-247 package. Reference FPCN# 16827.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAMS



MJH628x = Device Code

x = 4 or 7

A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device Order Number	Package Type	Shipping	
MJH6284G	TO-218 (Pb-Free)	30 Units / Rail	
MJH6287G	TO-218 (Pb-Free)	30 Units / Rail	
MJH6284G	TO-247 (Pb-Free)	30 Units / Rail	
MJH6287G	TO-247 (Pb-Free)	30 Units / Rail	

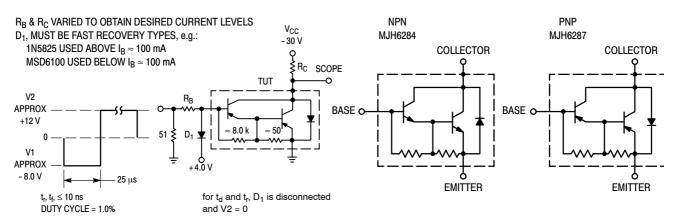
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (I _C = 0.1 Adc, I _B = 0)	V _{CEO(sus)}	100	_	Vdc	
Collector Cutoff Current (V _{CE} = 50 Vdc, I _B = 0)	I _{CEO}	-	1.0	mAdc	
	I _{CEX}	- -	0.5 5.0	mAdc	
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	2.0	mAdc	
ON CHARACTERISTICS (Note 1)					
DC Current Gain $ \begin{array}{l} \text{(I}_{C} = 10 \text{ Adc, V}_{CE} = 3.0 \text{ Vdc)} \\ \text{(I}_{C} = 20 \text{ Adc, V}_{CE} = 3.0 \text{ Vdc)} \end{array} $	h _{FE}	750 100	18,000 -	-	
Collector–Emitter Saturation Voltage (I _C = 10 Adc, I _B = 40 mAdc) (I _C = 20 Adc, I _B = 200 mAdc)	V _{CE(sat)}	- -	2.0 3.0	Vdc	
Base-Emitter On Voltage (I _C = 10 Adc, V _{CE} = 3.0 Vdc)	V _{BE(on)}	-	2.8	Vdc	
Base-Emitter Saturation Voltage (I _C = 20 Adc, I _B = 200 mAdc)	V _{BE(sat)}	-	4.0	Vdc	
DYNAMIC CHARACTERISTICS					
Current-Gain Bandwidth Product (I _C = 10 Adc, V _{CE} = 3.0 Vdc, f = 1.0 MHz)	f _T	4.0	-	MHz	
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz) MJH6284 MJH6287		- -	400 600	pF	
Small-Signal Current Gain (I _C = 10 Adc, V _{CE} = 3.0 Vdc, f = 1.0 kHz)	h _{fe}	300	-	-	

SWITCHING CHARACTERISTICS

			Тур	ical	
	Resistive Load	Symbol	NPN	PNP	Unit
Delay Time		t _d	0.1	0.1	μs
Rise Time	V_{CC} = 30 Vdc, I_{C} = 10 Adc $I_{B1} = I_{B2}$ = 100 mA	t _r	0.3	0.3	
Storage Time	Duty Cycle = 1.0%	t _s	1.0	1.0	
Fall Time		t _f	3.5	2.0	

^{1.} Pulse test: Pulse Width = 300 μ s, Duty Cycle = 2.0%.



For NPN test circuit reverse diode and voltage polarities.

Figure 2. Switching Times Test Circuit

Figure 3. Darlington Schematic

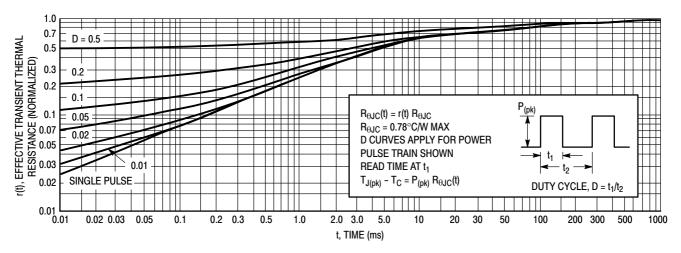


Figure 4. Thermal Response

FBSOA, FORWARD BIAS SAFE OPERATING AREA

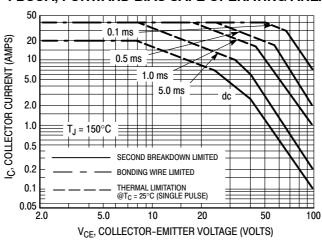


Figure 5. MJH6284, MJH6287

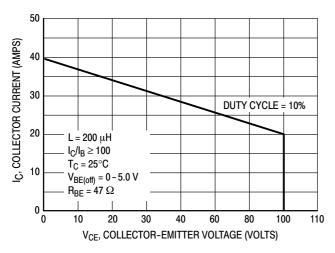


Figure 6. Maximum RBSOA, Reverse Bias Safe Operating Area

FORWARD BIAS

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

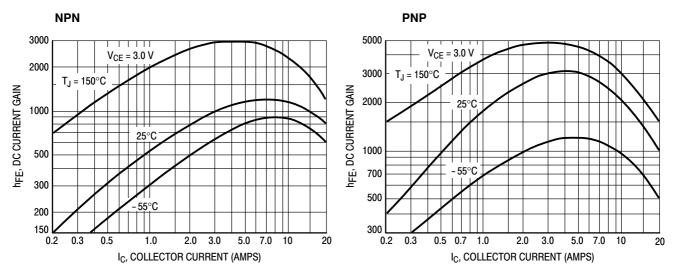


Figure 7. DC Current Gain

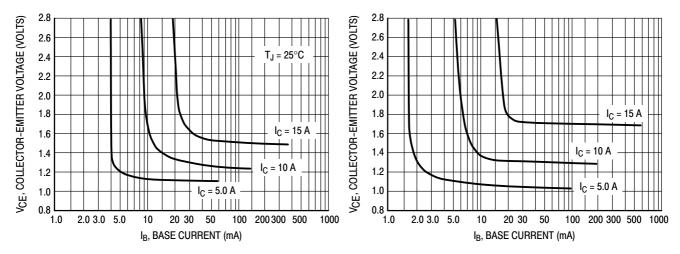


Figure 8. Collector Saturation Region

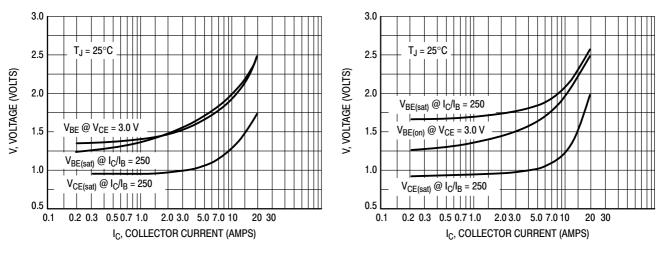
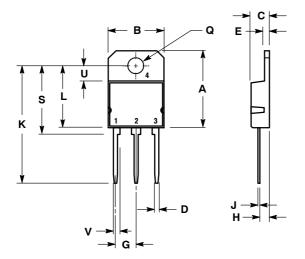


Figure 9. "On" Voltages

PACKAGE DIMENSIONS

SOT-93 (TO-218) CASE 340D-02 **ISSUE E**



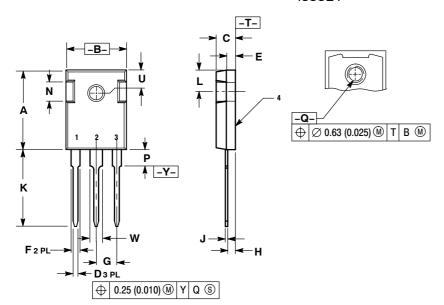
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		20.35		0.801
В	14.70	15.20	0.579	0.598
С	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
Н	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L		16.20		0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER

 - COLLECTOR

TO-247 CASE 340L-02 ISSUE F



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	20.32	21.08	0.800	8.30
В	15.75	16.26	0.620	0.640
С	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
Е	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45 BSC		0.215 BSC	
Н	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P		4.50		0.177
Q	3.55	3.65	0.140	0.144
U	6.15	BSC	0.242 BSC	
W	2.87	3.12	0.113	0.123

STYLE 3: PIN 1. BASE

- 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

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